NSR05T40XV2

500 mA, 40 V Schottky Barrier Diode

These Schottky barrier diodes are optimized for low forward voltage drop and low leakage current that offers the most optimal power dissipation in applications. They are housed in spacing saving micro−packaging ideal for space constraint applications.

Features

- Low Forward Voltage Drop − 530 mV (Typ.) @ I_F = 500 mA
- Low Reverse Current − 3.0 μA (Typ.) @ V_R = 40 V
- 500 mA of Continuous Forward Current
- ESD Rating: − Human Body Model: Class 3B
  − Charged Device Model: Class IV
- High Switching Speed
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- LCD and Keypad Backlighting
- Camera Photo Flash
- Buck and Boost dc−dc Converters
- Reverse Voltage and Current Protection
- Clamping & Protection

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	40	V
Forward Current (DC)	I_F	500	mA
Forward Surge Current (60 Hz @ 1 cycle)	I_{FSM}	3.0	A
Repetitive Peak Forward Current (Pulse Wave = 1 sec, Duty Cycle = 66%)	I_{FRM}	1.5	A
ESD Rating: Human Body Model Charged Device Model	ESD	> 8 > 1	kV

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

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SOD−523
CASE 502

MARKING DIAGRAM

YK = Specific Device Code
M = Date Code

ORDERING INFORMATION

Device	Package	Shipping†
NSR05T40XV2T5G	SOD−523 (Pb−Free)	8000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Min	Typ	Max	Unit
Thermal Resistance Junction–to–Ambient (Note 1) Total Power Dissipation @ T_A = 25°C	 $R_{\theta JA}$ P_D			 489 250	 °C/W mW
Thermal Resistance Junction–to–Ambient (Note 2) Total Power Dissipation @ T_A = 25°C	 $R_{\theta JA}$ P_D			 358 350	 °C/W mW
Junction and Storage Temperature Range	T_J, T_{stg}		–55 to +150		°C

1. Mounted onto a 4 in square FR−4 board 50 mm sq. 1 oz. Cu 0.06” thick single sided. Operating to steady state.
2. Mounted onto a 4 in square FR−4 board 650 mm sq. 1 oz. Cu 0.06” thick single sided. Operating to steady state.

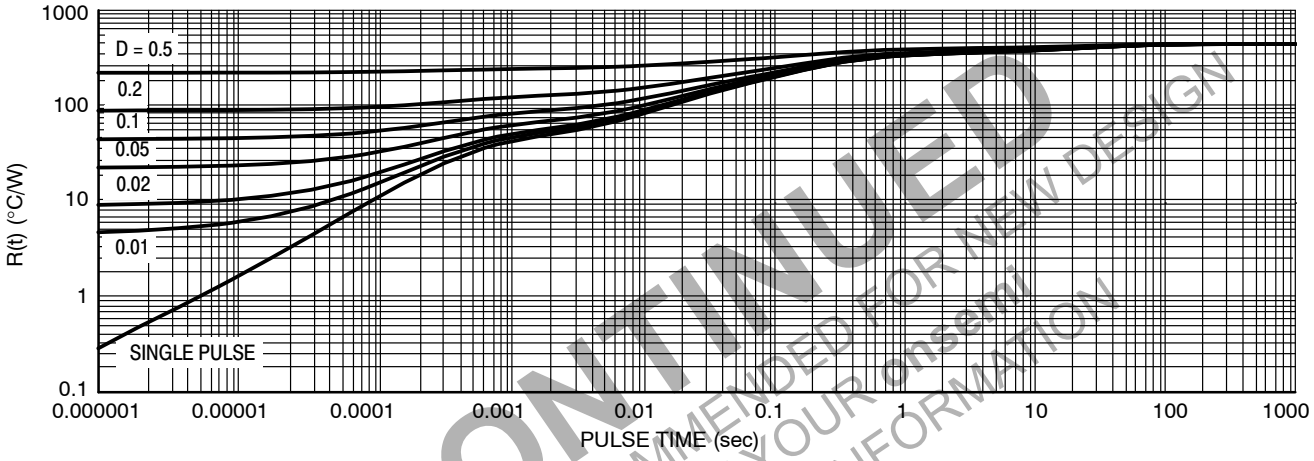


Figure 1. Thermal Response (Note 1)

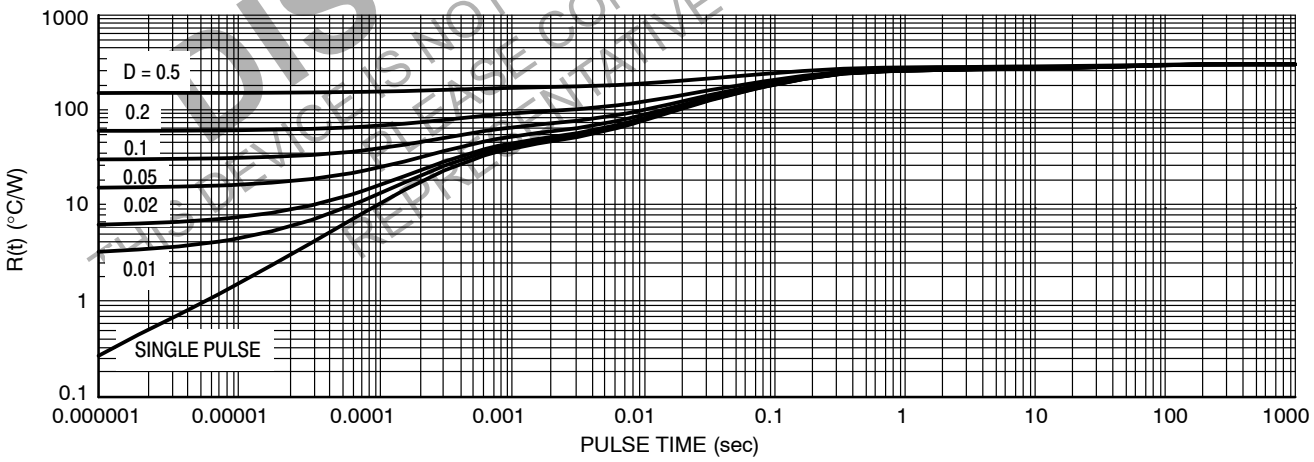
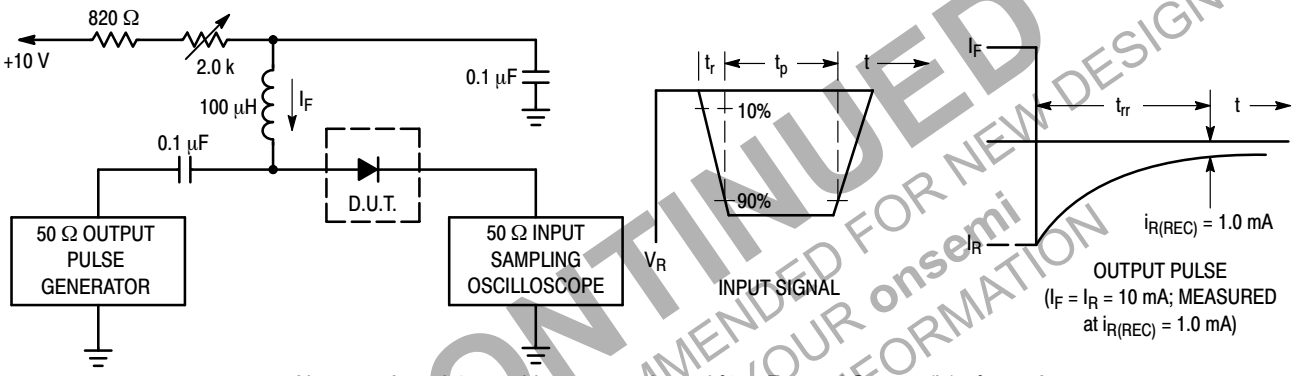


Figure 2. Thermal Response (Note 2)

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Leakage (V_R = 10 V) (V_R = 40 V)	I_R		 0.5 3.0	 5.0 55	μA
Forward Voltage (I_F = 10 mA) (I_F = 100 mA) (I_F = 200 mA) (I_F = 500 mA)	V_F		 360 420 450 530	 400 465 525 640	mV
Total Capacitance (V_R = 1.0 V, f = 1.0 MHz)	C_T		70		pF
Reverse Recovery Time (I_F = I_R = 10 mA, $I_{R(REC)}$ = 1.0 mA, Figure 3)	t_{rr}		20		ns
Peak Forward Recovery Voltage (I_F = 100 mA, t_r = 20 ns, Figure 4)	V_{FRM}		540		mV



Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 10 mA.
2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 10 mA.
3. $t_p \gg t_{rr}$

Figure 3. Recovery Time Equivalent Test Circuit

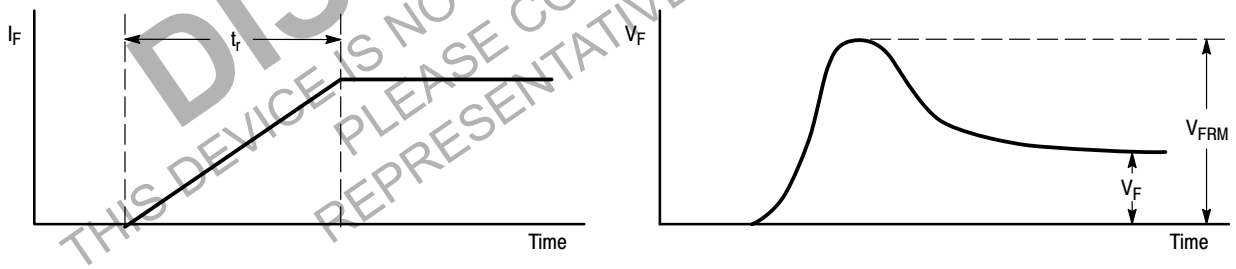


Figure 4. Peak Forward Recovery Voltage Definition

TYPICAL CHARACTERISTICS

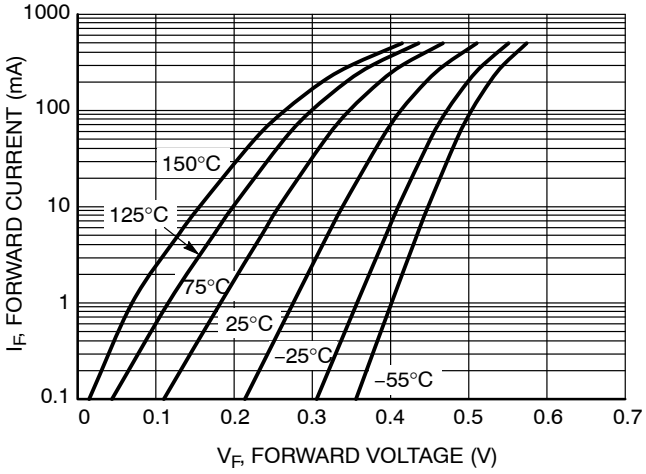


Figure 5. Forward Voltage

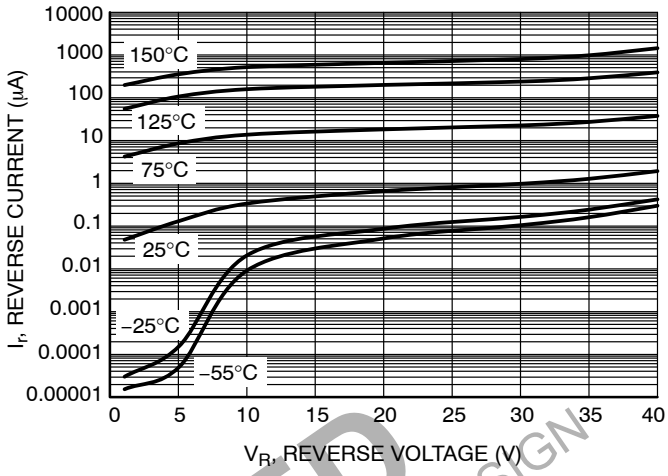


Figure 6. Leakage Current

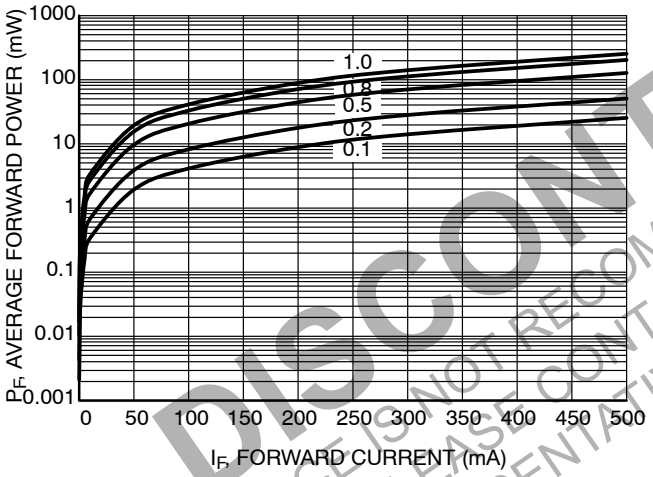


Figure 7. Average Forward Power Dissipation

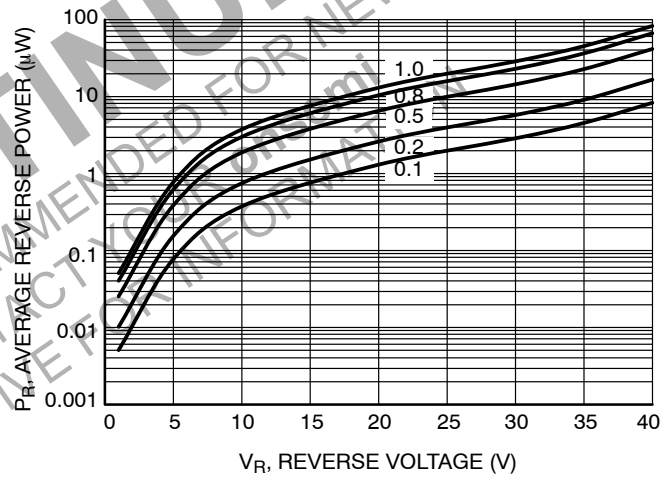


Figure 8. Average Reverse Power Dissipation

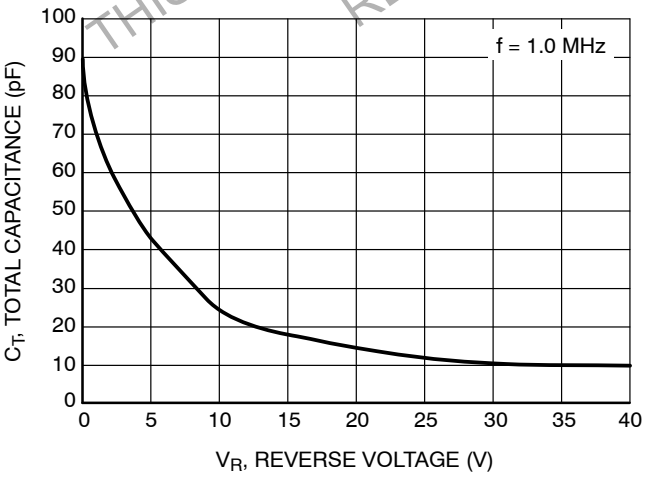


Figure 9. Total Capacitance

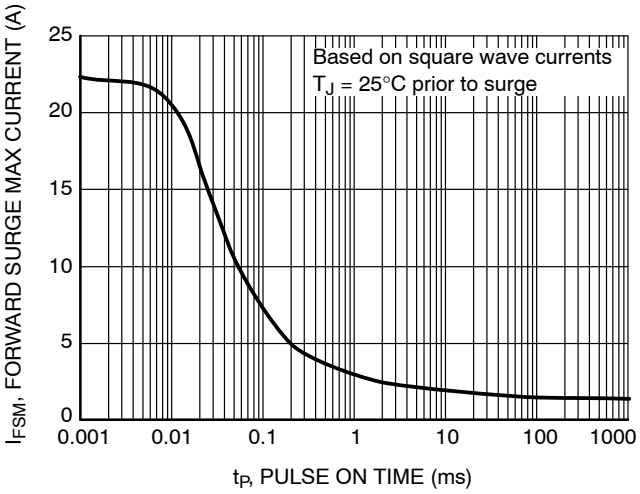


Figure 10. Forward Surge Current

ADDITIONAL INFORMATION

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Technical Library: www.onsemi.com/design/resources/technical−documentation
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